



NE202930

Data Sheet R09DS0003EJ0100 Rev.1.00 Jul 14, 2010

Silicon NPN Epitaxial High Frequency Transistor

FEATURES

- High transition frequency $f_T = 11$ GHz TYP.
- Ideal for low noise and low distortion amplification
- Suitable for equipments of low collector voltage (Less than 5 V)
- Suitable for up to 1 GHz applications

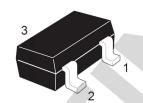
APPLICATIONS

• LNA (Low Noise Amplifier) or power splitter for digital-TV

OUTLINE

RENESAS Package code: 30

(Package name: 3-pin super minimold (30 PKG))



- 1. Emitter
- 2. Base
- 3. Collector

Note: Marking is "R7D"

ORDERING INFORMATION

Part Number	Order Number	Package	Marking	Supplying Form
NE202930-T1	NE202930-T1-A	3-pin super	R7D	Embossed tape 8 mm wide
		minimold (30 PKG)		Pin 3 face the perforation side of the tape
		(Pb-Free)		Qty 3 kpcs/reel

Remark To order evaluation samples, please contact your nearby sales office.

Part number for sample order: NE202930-A

ABSOLUTE MAXIMUM RATINGS ($T_A = +25$ °C)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	V_{CBO}	9	V
Collector to Emitter Voltage (Base Short)	V _{CES}	9	V
Collector to Emitter Voltage (Base Open)	V _{CEO}	6	V
Emitter to Base Voltage	V_{EBO}	2	V
Collector Current	Ic	100	mA
Total Power Dissipation Note	P _{tot}	150	mW
Junction Temperature	Tj	150	°C
Storage Temperature	T _{stg}	-65 to +150	°C

Note: Free air

CAUTION

Observe precautions when handling because these devices are sensitive to electrostatic discharge.



ELECTRICAL CHARACTERISTICS ($T_A = +25$ °C, unless otherwise specified)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
DC Characteristics						
Collector Cut-off Current	I _{CBO}	V _{CB} = 5 V, I _E = 0	-	-	100	nA
Emitter Cut-off Current	I _{EBO}	$V_{EB} = 1 \text{ V}, I_{C} = 0$	-	-	100	nA
DC Current Gain	h _{FE} Note1	$V_{CE} = 5 \text{ V}, I_{C} = 5 \text{ mA}$	85	140	205	_
RF Characteristics	RF Characteristics					
Gain Bandwidth Product	f _T	$V_{CE} = 5 \text{ V}, I_{C} = 30 \text{ mA}, f = 1 \text{ GHz}$	-	11.0	-	GHz
Insertion Power Gain	$ S_{21e} ^2$	$V_{CE} = 5 \text{ V}, I_{C} = 30 \text{ mA}, f = 1 \text{ GHz}$	11.5	13.5	_	dB
Noise Figure (1)	NF1	$V_{CE} = 5 \text{ V}, I_{C} = 5 \text{ mA}, f = 1 \text{ GHz},$	-	1.15	1.5	dB
		$Z_S = Z_{Sopt}, Z_L = 50 \Omega$				
Noise Figure (2)	NF2	$V_{CE} = 5 \text{ V}, I_{C} = 30 \text{ mA}, f = 1 \text{ GHz},$	-	1.5	-	dB
		$Z_{\rm S} = Z_{\rm Sopt}, Z_{\rm L} = Z_{\rm Lopt}$				
Associated Gain (1)	G _a 1	$V_{CE} = 5 \text{ V}, I_{C} = 5 \text{ mA}, f = 1 \text{ GHz},$	10.0	12.0	-	dB
		$Z_S = Z_{Sopt}, Z_L = 50 \Omega$				
Associated Gain (2)	G_a2	$V_{CE} = 5 \text{ V}, I_{C} = 30 \text{ mA}, f = 1 \text{ GHz},$	-	13.5	-	dB
		$Z_{\rm S} = Z_{\rm Sopt}, Z_{\rm L} = Z_{\rm Lopt}$				
Reverse Transfer Capacitance	C _{re} Note 2	$V_{CB} = 5 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$	4	0.6	8.0	pF
Maximum Stable Power Gain	MSG Note 3	$V_{CE} = 5 \text{ V}, I_{C} = 30 \text{ mA}, f = 1 \text{ GHz}$	13.5	15.5	_	dB
Gain 1 dB Compression Output	P _{O (1 dB)}	$V_{CE} = 5 \text{ V}, I_{C \text{ (set)}} = 30 \text{ mA}, f = 1 \text{ GHz},$	-	19	_	dBm
Power		$Z_S = Z_{Sopt}, Z_L = Z_{Lopt}$				
Output 3rd Order Intercept Point	OIP ₃	$V_{CE} = 5 \text{ V}, I_{C \text{ (set)}} = 30 \text{ mA}, f = 1 \text{ GHz},$	_	32		dBm
		$\Delta f = 1 \text{ MHz}, Z_S = Z_{Sopt}, Z_L = Z_{Lopt}$				

Notes: 1. Pulse measurement: PW \leq 350 μ s, Duty Cycle \leq 2%

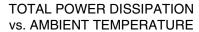
2. Collector to base capacitance when the emitter grounded.

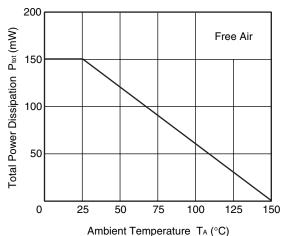
3. MSG =
$$\left| \frac{S_{21}}{S_{12}} \right|$$

hfe CLASSIFICATION

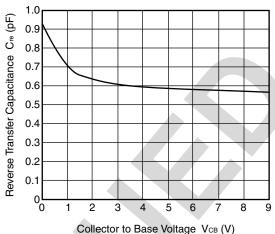
Rank	YFB
Marking	R7D
h _{FE} Value	85 to 205

TYPICAL CHARACTERISTICS (T_A = +25°C, unless otherwise specified)

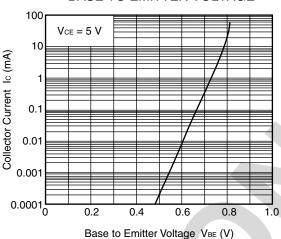




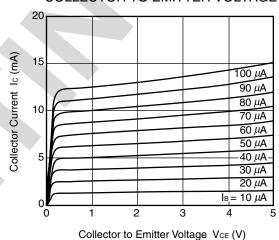
REVERSE TRANSFER CAPACITANCE vs. COLLECTOR TO BASE VOLTAGE



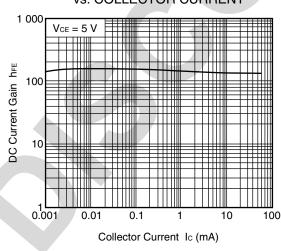
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



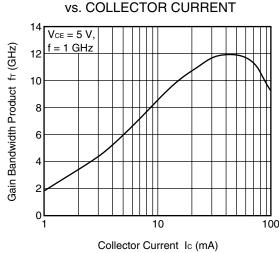
COLLECTOR CURRENT vs.
COLLECTOR TO EMITTER VOLTAGE



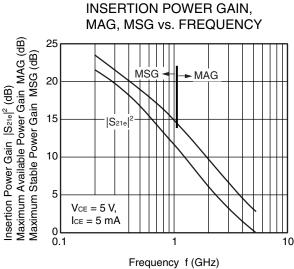
DC CURRENT GAIN vs. COLLECTOR CURRENT

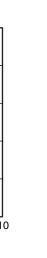


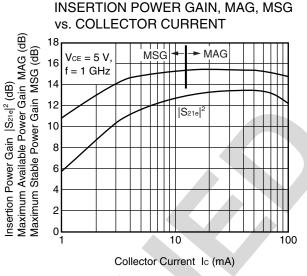
GAIN BANDWIDTH PRODUCT

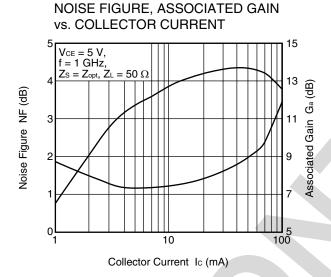


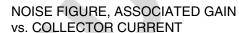
Remark The graphs indicate nominal characteristics.

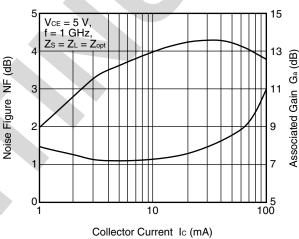




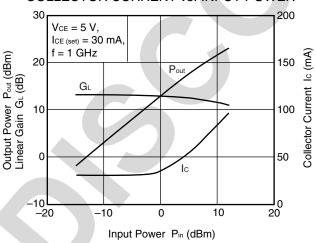




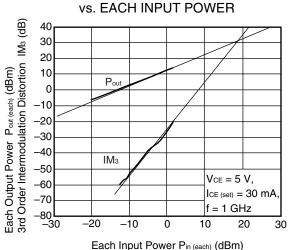








EACH OUTPUT POWER, IM3



Remark The graphs indicate nominal characteristics.

S-PARAMETERS

S-parameters and noise parameters are provided on our Web site in a format (S2P) that enables the direct import of the parameters to microwave circuit simulators without the need for keyboard inputs.

Click here to download S-parameters.

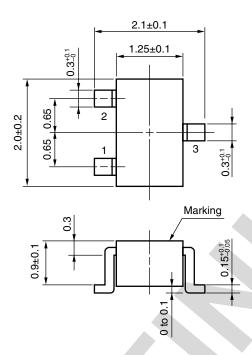
[RF and Microwave] \rightarrow [Device Parameters]

URL http://www2.renesas.com/microwave/en/download.html



PACKAGE DIMENSIONS

3-PIN SUPER MINIMOLD (30 PKG) (UNIT: mm)



PIN CONNECTIONS

- 1. Emitter
- 2. Base
- 3. Collector

NE202930 Data Sheet

		Description		
Rev.	Date	Page	Summary	
1.00	Jul 14, 2010	_	First edition issued	



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